

Amendments to the Specification (other than claims):

Please replace paragraph [0003] with the following amended paragraph:

[0003] For example, a semiconductor wafer heating device equipped with a ceramic susceptor in which a resistive heating element is embedded and that is installed within a reaction chamber, and with a pillar-like support member provided on a surface of the susceptor apart from its wafer-heating face and that forms a gastight seal between it and the chamber, is proposed in Japanese ~~Pat. App.~~ Pre-Grant Pub. No. H06-28258.

Please replace paragraph [0026] with the following amended paragraph:

[0026] It should be understood that in manufacturing the ceramic susceptors represented in Figs. [[3]] 2 and 3, apart from the method of joining the respective ceramic substrates, green sheets of approximately 0.5 mm thickness may be prepared, and after print-coating an electrically conductive paste into circuit patterns for a resistive heating element and/or a plasma electrode onto the green sheets, these green sheets and, as needed, ordinary green sheets may be laminated to produce the required thickness, and made unitary by sintering them simultaneously.

Please replace paragraph [0045] with the following amended paragraph:

[0045] Disk pairs of ceramic-susceptor AlN substrates 330 mm in diameter, made out of aluminum nitride sinters, were prepared by the same method as in Embodiment 1.

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In utilizing the AlN substrate pairs to fabricate ceramic susceptors, the material for the resistive heating element provided was changed to Mo, to Pt, to Ag–Pd, and to Ni–Cr, and respective pastes were printed-coated onto a face of first disks from the AlN substrate pairs, which were then baked in a non-oxidizing atmosphere.